OV Semiconductor

Single P-Channel, -20V, -3.0A, Power MOSFET

Features

V_{DS} (V)	Typical $R_{DS(on)}$ (mΩ)
-20	65 @ V_{GS}=-4.5V
	75 @ V_{GS}=-2.5V

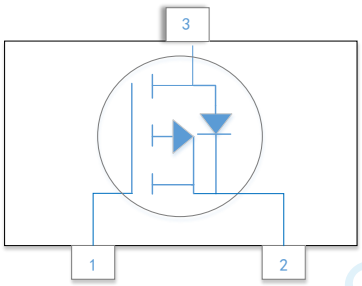
- ✧ Trench Technology
- ✧ Supper high density cell design
- ✧ Excellent on resistance
- ✧ Extremely Low Threshold Voltage
- ✧ Small package SOT-23

Applications

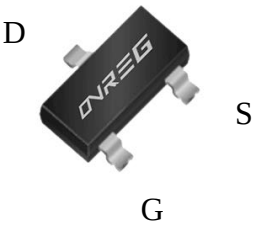
- ✧ DC/DC converters
- ✧ Power supply converters circuit
- ✧ Load/Power Switching for portable device

Mechanical Data

- ✧ UL Flame Rating : UL94V-0
- ✧ Reel Size : 7 inch
- ✧ RoHS/WEEE Compliant



Circuit Diagram



SOT-23

Absolute Maximum Rating (Ta=25℃, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current	I_D	-3.0	A
Pulsed Drain Current (t=300μs)	I_{DM}	-10	A
Power Dissipation	P_D	0.4	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	312.5	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~ +150	℃

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Thermal resistance ratings(Ta=25℃, unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =-250μA	-20			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =-20V,V_{GS} = 0V			-1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±12V, V_{DS} = 0V			±100	nA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-0.5	-0.7	-1.5	V
Drain-source on-resistance[a]	$R_{DS(on)}$	V_{GS} =-4.5V, I_D =-3A		65	70	mΩ
		V_{GS} =-2.5V, I_D =-2A		75	90	
Forward tranconductance[a]	g_{FS}	V_{DS} =-5V, I_D =-2A	5			S
Dynamic characteristics[b]						
Input Capacitance	C_{iss}	V_{DS} =-12V,V_{GS} =0V,f =1MHz		405		pF
Output Capacitance	C_{oss}			75		
Reverse Transfer Capacitance	C_{rss}			55		
Gate resistance	R_g	f =1MHz		6		Ω
Total Gate Charge	Q_g	V_{DS} =-12V,V_{GS} =-2.5V,I_D=-3A		3.3	12	nC
Gate-Source Charge	Q_{gs}			0.7		
Gate-Drain Charge	Q_{gd}			1.3		
Turn-on delay time	$t_{d(on)}$	V_{DD}=-12V,V_{GEN}=-4.5V,I_D=-1A R_L=10Ω,R_{GEN}=1Ω		11		ns
Turn-on rise time	t_r			35		
Turn-off delay time	$t_{d(off)}$			30		
Turn-off fall time	t_f			10		
Source-Drain Diode characteristics						
Diode forward current	I_S	T_C=25℃			-2.3	A
Diode pulsed forward current[a]	I_{SM}				-10	A
Diode Forward voltage	V_{DS}	V_{GS} =0V, I_S=-1.3A			-1.2	V

Notes :

a.Pulse Test : Pulse Width < 300μs, Duty Cycle ≤2%.

b.Guaranteed by design, not subject to production testing.

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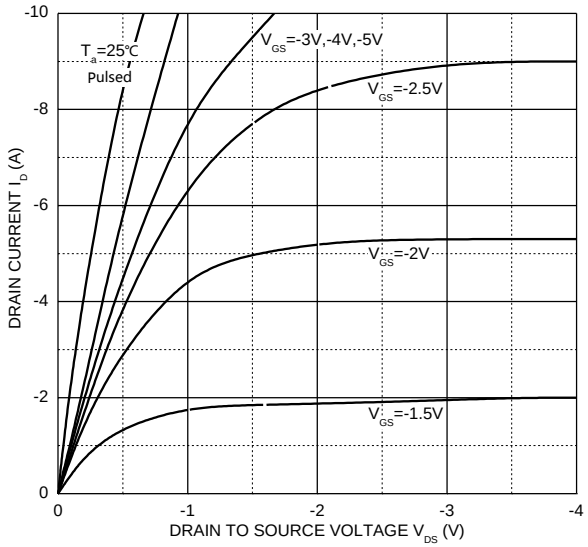
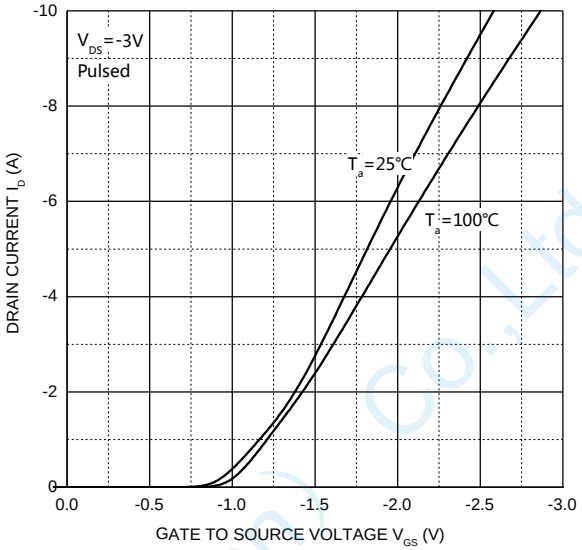
Electronics Characteristics (Ta=25℃, unless otherwise noted)

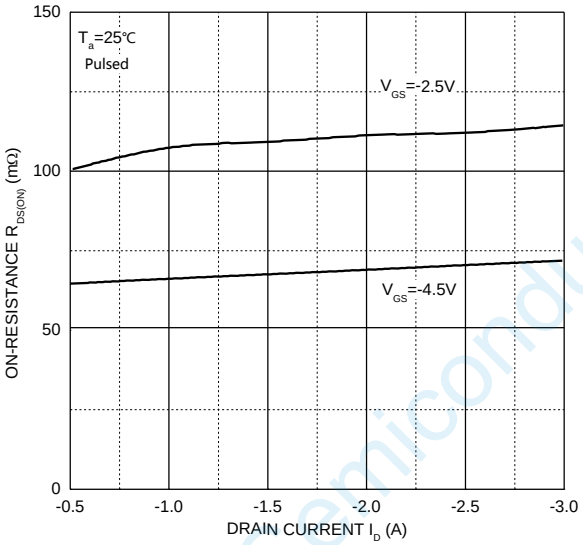
Output Characteristics



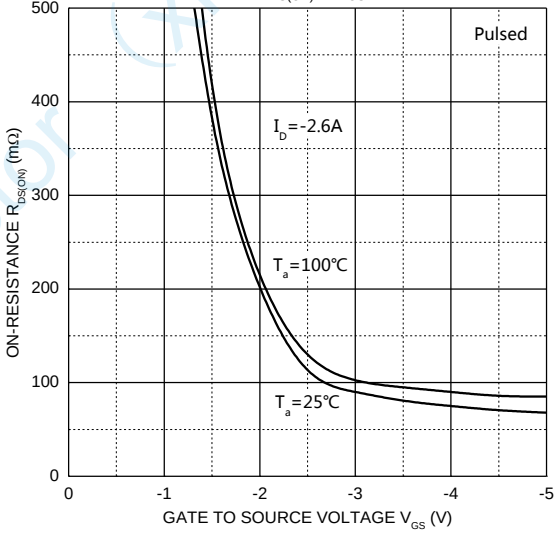
Transfer Characteristics



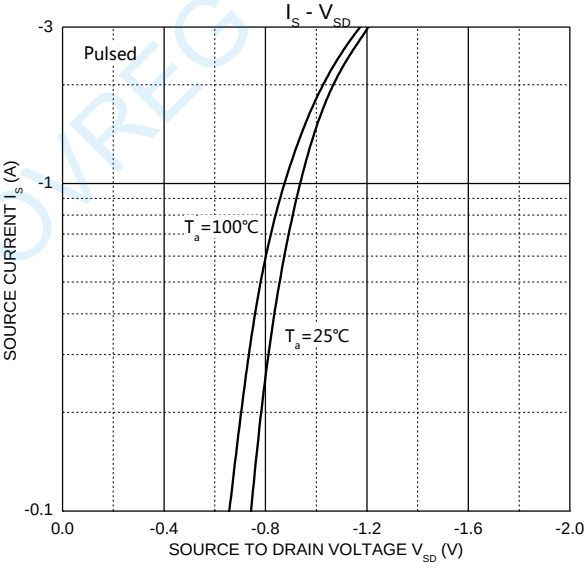
$R_{DS(ON)}$ – I_D



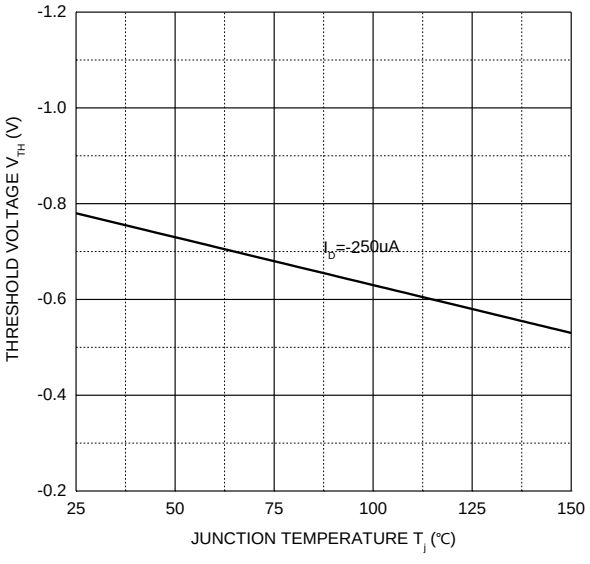
$R_{DS(ON)}$ - V_{GS}



I_S - V_{SD}



Threshold Voltage



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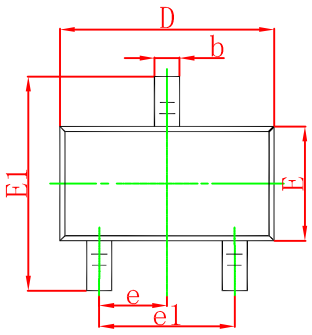
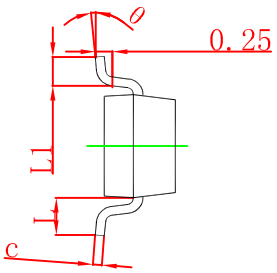
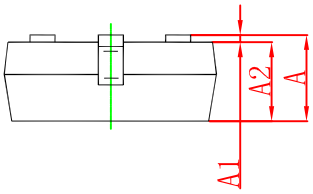
Package information

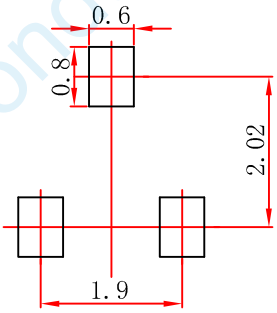






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Recommend PCB Layout



Notes: This PCB Layout Is For Reference Purposes Only

Marking



Ordering Information

Part number	Material	Type	Reel size	MOQ	MOQ/internal box	MOQ/carton
OVM20P80T	GREEN	T/R	7 inch	3k/reel	10reel= 30k/box	4boxes=120k/carton

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